

			l	/acuum tubes (Diode and Triode)								
1.	Thermionic emission from	n a heated filament varies with	n its temperature <i>T</i> as	[CBSE 1990; RPMT 2000; CPMT 2002]								
	(a) $T^{-1}$	(b) <i>T</i>	(c) $T^2$	(d) $T^{3/2}$								
2.	Number of secondary elec	ctrons emitted per number of	primary electrons depends on	[RPET 2000]								
	(a) Material of target		(b) Frequency of primary	y electrons								
	(c) Intensity		(d) None of the above									
3.	Due to S.C.R in vacuum t	ube		[RPET 2000]								
	(a) $I_p \rightarrow \text{Decrease}$	(b) $I_p$ - Increase	(c) $V_p = Increase$	(d) $V_g = $ Increase								
4.	In diode, when there is sa	turation current, the plate res	istance $(r_p)$ is	[AIIMS 1997; Haryana PMT 2000]								
	(a) Zero	(b) Infinite	(c) Some finite quantity	(d) Data is insufficient								
5.	The grid voltage of any tri plate circuit current will be		volt to - 3 volt and the mutual condu	uctance is $3 \times 10^{-4}$ <i>mho</i> . The change in <b>[MNR 1999]</b>								
	(a) 0.8 <i>mA</i>	(b) 0.6 <i>mA</i>	(c) 0.4 <i>mA</i>	(d) 1 <i>mA</i>								
6.	In a triode, $g_m = 2 \times 10^{-3} ohm^{-1}$ ; $\mu = 42$ , resistance load, $R = 50$ kilo ohm. The voltage amplification obtained from this triode											
	be											
				[MNR 1999]								
	(a) 30.42	(b) 29.57	(c) 28.18	(d) 27.15								
7.	In an amplifier the load re	sistance $R_L$ is equal to the pl	late resistance $(r_p)$ . The voltage amplitude $r_p$	plification is equal to [CPMT 1995]								
	(a) $\mu$	(b) $2\mu$	(c) $\mu / 2$	(d) $\mu / 4$								
8.	For a given plate-voltage,	the plate current in a triode is	s maximum when the potential of	[IIT-JEE 1985; CPMT 1995; AFMC 1999]								
	(a) The grid is positive a	nd plate is negative	(b) The grid is positive a	and plate is positive								
	(c) The grid is zero and p	plate is positive	(d) The grid is negative	and plate is positive								
9.	If $R_p = 7 K\Omega$ , $g_m = 2.5$ millimho, then on increasing plate voltage by $50 V$ , how much the grid voltage is changed so that plate											
	current remains the same			[RPET 1996]								
	(a) - 2.86 V	(b) - 4 V	(c) +4 V	(d) +2 V								
10.		f a triode is 20 and trans-cond	ductance is 3 milli mho and load resis	stance $3 \times 10^4 \Omega$ , then the voltage gain								
	IS			[RPMT 1996]								
	(a) 16.36	(b) 28	(c) 78	(d) 108								
11.		` '		e input signal voltage is 0.5 volt, then								
•	output signal voltage will I			[RPMT 1995]								
	(a) 1.25 <i>volt</i>	(b) 5 <i>volt</i>	(c) 2.5 <i>volt</i>	(d) 10 <i>volt</i>								
	(-, ,	(2) 3.3	(5) 2.3 75%	(4)								

100						
186	Valve & Digital Electro	onics				
12.	The amplification factor voltage is to be increase	of a triode is 20. If the grid potentied by	ial is reduced	d by 0.2 <i>volt</i> then to I	keep the plate curre	nt constant its plate [RPMT 1993, 95]
	(a) 10 <i>volt</i>	(b) 4 <i>volt</i>	(c)	40 volt	(d) 100 <i>voli</i>	t
13.	For a triode $r_p = 10$ kilo	o ohm and $g_m = 3$ milli mho. If the	load resista	nce is double of plat	te resistance, then t	he value of voltage
	gain will be					[RPMT 1994]
	(a) 10	(b) 20	(c)	15	(d) 30	
14.	The amplification produ	ced by a triode is due to the action	n of			[AFMC 1994]
	(a) Filament	(b) Cathode	(c)	Grid	(d) Plate	
12. The vo (a) (a) (a) (a) (a) (a) (a) (b) (c) (d) (a) (a) (a) (a) (a) (a) (a) (a) (a) (a	In an experiment, the sa current. It can be done,	aturation in the plate current in a d if	liode is obse	rved at 240 V. But a	student still wants to	o increase the plate [MNR 1994]
	(a) The plate voltage is	s increased further	(b)	The plate voltage is	decreased	
	(c) The filament currer	nt is decreased	(d)	The filament current	t is increased	
16.	In a triode amplifier, the	value of maximum gain is equal to	0			[MP PMT 1992]
	(a) Half the amplification	on factor		(b)	Amplification	n factor
	(c) Twice the amplifica	ation factor	(d)	Infinity		
17.	For a given triode $\mu = 2$	20 . The load resistance is 1.5 time	es the anode	resistance. The max	kimum gain will be	[CPMT 1992]
	(a) 16	(b) 12	(c)	10	(d) None of	the above
18.	The amplification factor	of a triode is 20. Its plate resistance	ce is 10 kilo	ohms. Mutual condu	ctance is	
	(a) $2 \times 10^5  mhos$	(b) $2 \times 10^4 \ mhos$	(c)	500 <i>mhos</i>	(d) $2 \times 10^{-3}$	mhos
19.	The voltage gain of a tri	ode depends upon				[CPMT 1992]
	(a) Filament voltage	(b) Plate voltage	(c)	Plate resistance	(d) Plate cu	ırrent
20.	In a triode valve					[MP PET 1992]
	• •	s zero then plate current will be ze				
	• •	of filament is doubled, then the the				
	• •	of filament is doubled, then the the		•		
	, ,	oltage the plate current varies with		_		
21.	The plate current $i_p$ in a	a triode valve is given $i_p = K(V_p)$	$+\mu V_g)^{3/2}$	where $i_{\rho}$ is in milliar	mpere and $V_{ ho}$ and $1$	$V_g$ are in <i>volt</i> . If $r_p$ =
	104 <i>ohm</i> , and $g_m = 5 \times$	$< 10^{-3}  mho$ , then for $i_p = 8  mA$ and	$nd V_p = 300$	volt, what is the va	llue of $K$ and grid ${\sf cut}$	t off voltage
						[Roorkee 1992]
	(a) $-6 V$ , $(30)^{3/2}$	(b) $-6V,(1/30)^{3/2}$	(c)	+ 6 V, (30) <sup>3/2</sup>	(d) $+ 6 V$ , (1	/30) <sup>3/2</sup>
22.	The amplification factor keep the plate current c	of a triode valve is 15. If the gricenstant (in volt) is	d voltage is o	changed by 0.3 volt	the change in plate	voltage in order to
	(a) 0.02	(b) 0.002	(c)	4.5	(d) 5.0	
23.	The slopes of anode ar factor of the valve	nd mutual characteristics of a triod	de are 0.02 <i>i</i>	$mA V^1$ and 1 $mA V^1$	respectively. What	is the amplification [MP PMT 1990]
	(a) 5	(b) 50	(c)	500	(d) 0.5	
24.	The slope of plate cha	aracteristic of a vacuum tube die	ode for cert	ain operating point	on the curve is 10	$0^{-3}  rac{mA}{V}$ . The plate
	resistance of the diode	and its nature respectively				

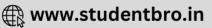
24. The slope of plate characteristic of a vacuum tube diode for certain operating point on the curve is 10<sup>-3</sup> mA/V. The plate resistance of the diode and its nature respectively

(a) 100 kilo-ohms static
(b) 1000 kilo-ohms static
(c) 1000 kilo-ohms dynamic
(d) 100 kilo-ohms dynamic

25. A triode has a mutual conductance of 2×10<sup>-3</sup> mho and an amplification factor of 50. The anode is connected through a resistance of 25×10<sup>3</sup> ohms to a 250 volts supply. The voltage gain of this amplifier is [MP PMT 1989]

(a) 50
(b) 25
(c) 100
(d) 12.5

26. 14×10<sup>15</sup> electrons reach the anode per second. If the power consumed is 448 milliwatts, then the plate (anode) voltage is [MP PMT 1989]



							Valve & Digi	tal Electronics 187					
	(a) 150 V	(b)	200 <i>V</i>		(c)	$14 \times 448 V$	(d) 448/	14 <i>V</i>					
27.	A valve oscillator is							[MP PMT 1988]					
	(a) Simple diode	(b)	Double diode		(c)	Triode	(d) <i>L-C</i>	circuit					
28.	Amplification factor of a triode that plate current remains cor		-	tage is red	luced by o	one volt, how much	should the plate v	oltage be increased so					
	(a) 10 V	(b)	1/10 <i>V</i>		(c)	1/20 V	(d) 20 l	′					
29.	If the amplification factor of a	triode	valve is 100, t	hen at plat	te potentia	al of 250 <i>volt</i> the cut	toff voltage of its g	rid will be [MP PET 1989					
	(a) 0 V	(b)	-0.4 V		(c)	-2.5 V	(d) - 150	) <i>V</i>					
30.	In the circuit of a triode valve volt and the grid potential is d		-	-				d from 200 <i>volt</i> to 220					
	(a) 15	(b)	20		(c)	25	(d) 35						
31.	If the amplification factor of a mho is	triod	e ( $\mu$ ) is 22 and	its plate r	resistance	e is 6600 <i>ohm</i> , then	the mutual condu	uctance of this valve is					
								[MP PMT 1989]					
	(a) $\frac{1}{300}$	(b)	$25 \times 10^{-2}$		(c)	$2.5 \times 10^{-2}$	(d) 0.25	$\times 10^{-2}$					
32.	For a triode, at $V_g = -1$ volt,	the fo	llowing observa	ations wer	e taken <i>V</i>	$V_p = 75  V, I_p = 2mA$ ,	$V_p = 100  V, I_p = 41$	nA . The value of plate					
	resistance will be							[MP PMT 1989]					
	(a) 25 KΩ	(b)	$20.8$ Κ $\Omega$		(c)	12.5 KΩ	(d) 100	KΩ					
33.	The triode constant is out of the	he foll	lowing					[RPMT 1989]					
	(a) Plate resistance	(b)	Amplification	factor	(c)	Mutual conductano	ce (d) All th	ne above					
34.	The unit of mutual conductand	ce of	a triode valve is	6				[MP PMT 1988]					
	(a) Siemen	(b)	Ohm		(c)	Ohm metre	(d) Joul	e Coulomb¹					
35.	With a change of load resista changes from 25 to 30. Plate				mplifier, fr	rom 50 <i>kilo ohms</i> to	o 100 <i>kilo ohms</i> , it	s voltage amplification [MP PET 1986]					
	(a) 25 Kilo ohms	(b) 75 Kilo ohms			(c)	7.5 Kilo ohms	(d) 2.5 /	Kilo ohms					
36.	The linear portions of the cha	racter	ristic curves of a	a triode va	lve give th	ne following reading	js –	[Roorkee 1985]					
	$V_g$ ( volt)	0	- 2	- 4	- 6								
	$I_p(mA)$ for $V_p = 150$ volts	15	12.5	10	7.5								
	$I_p(mA)$ for $V_p = 120$ volts	10	7.5	5	2.5								
	The plate resistance is												
	(a) 2000 <i>ohms</i>	(b)	4000 <i>ohms</i>		(c)	8000 <i>ohms</i>	(d) 6000	) ohms					
37.	The amplification factors of a potential, so that the current r			grid poten	itial is red	uced by 0.4 volt the	en what should b	e the increase in plate [RPET 1984]					
	(a) 0.4 V	(b)	40 V		(c)	4 <i>V</i>	(d) 14 l	/					
38.	Select the correct statements	from	the following					[IIT-JEE 1984]					
	(a) A diode can be used as a	a recti	fier										
	(b) A triode cannot be used as a rectifier												
	(c) The current in a diode is always proportional to the applied voltage												
	(d) The linear portion of the	I-V ch	aracteristic of a	triode is u	used for a	mplification without	distortion						
39.	The output current versus time curve of a rectifier is shown in the figure. The average value of the output current in this case is												
	•				<b>J</b> ·	Ů,	,	[AIIMS 1982]					
	(a) 0					tent ↑							

## 188 Valve & Digital Electronics

- (b)  $\frac{i_0}{\pi}$
- (c)  $\frac{2i_0}{\pi}$
- (d) i<sub>0</sub>
- 40. The introduction of a grid in a triode valve affects plate current by

[CPMT 1975, 90]

- (a) Making the thermionic emission easier at low temperature
- (b) Releasing more electrons from the plate

(c) By increasing plate voltage

- (d) By neutralising space charge
- **41.** Before the saturation state of a diode at the plate voltages of 400 V and 200 V respectively the currents are  $i_1$  and  $i_2$  respectively. The ratio  $i_1/i_2$  will be
  - (a)  $\sqrt{2}/4$
- (b)  $2\sqrt{2}$

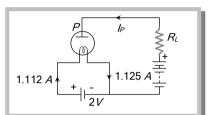
(c) 2

(d) 1/2

- **42.** The value of constant A in Richardson-Dushman equation in  $A/m^2/k^2$  is
  - (a)  $\frac{4\pi me}{h^3}$
- (b)  $\frac{4 \pi m e^2}{h^3}$

- (c)  $\frac{4\pi me^2 k}{h^3}$
- (d)  $\frac{4\pi nk^2 e}{h^3}$

43. The value of plate current in the given circuit diagram will be



- (a) 3 *mA*
- (b) 8 *mA*
- (c) 13 mA
- (d) 18 mA
- **44.** The plate resistance of a diode valve is 5000  $\Omega$ . If the value of plate current is 4.5 mA at a plate potential of 70 V, then what will be the plate potential at plate current of 6.5 mA
  - (a) 60 V

(b) 70 V

- (c) 80 V
- (d) 90 V

45. A certain triode shows the following readings

	•	9
$V_{ ho}$	$V_g$	$I_{p}$
150 V	-2 V	5 <i>mA</i>
150 V	- 3.5 V	3.2 <i>m</i> A
195 V	-35 V	5 <i>mA</i>

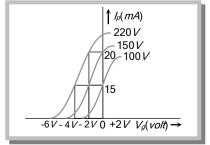
The amplification factor of the triode is

(a) 22.5

(b) 45

(c) 30

- (d) 60
- **46.** The relation between dynamic plate resistance  $(r_p)$  of a vacuum diode and plate current in the space charge limited region, is
  - (a)  $r_p \propto I_p$
- (b)  $r_p \propto I_p^{3/2}$
- (c)  $r_p \propto \frac{1}{I_-}$
- (d)  $r_p \propto \frac{1}{(L)^{1/3}}$
- 47. The voltage gain of a triode amplifier is 50. An input signal of  $V_g = 20 \sin \omega t \, mV$  is applied in the grid circuit. The output voltage will be
  - (a)  $-1000 \sin \omega t V$
- (b)  $-50 \sin \omega t V$
- (c)  $-20 \sin \omega t V$
- (d)  $-\sin \omega t V$
- 48. The mutual characteristic curves of a triode are shown in the following figure. The ac mutual conductance of triode will be
  - (a) 2.5 *m mho*
  - (b) 5.0 *m mho*
  - (c) 7.5 m mho
  - (d) 10.0 m mho



- **49.** An a.c. signal of IV (r.m.s.) and frequency 1 KHz is applied to the grid of a triode. If, for the triode  $\mu = 24$ ,  $r_p = 10$   $k\Omega$  and  $R_L = 10$   $k\Omega$ , then the voltage gain of the amplifier will be
  - (a) 4

(b) 8

(c) 12

(d) 16



50. Mutual characteristic curves in working field of triode are parallel lines.

When  $V_p = 200$  V value of plate current  $i_p = (3 V_g + 10) mA$  and when  $V_p = 150$ , V value of plate current  $i_p = (3 V_g + 6) mA$ Application factor of triode value is

(a) 12.5

(b) 4.33

(c) 15.5

(d) 37.5

Logic gates

[MP PET 2004]

51. How many NAND gates are used to form an AND gate

(a) 1

(b) 2

(c) 3

(d) 4

52. A gate has the following truth table

) 3

[CBSE PMT 2000]

P 1 1 0 0

Q 1 0 1 0

R 1 0 0 0

The gate is

(a) NOR

(b) OR

- (c) NAND
- (d) AND

53. A logic gate is an electronic circuit which

- (a) Makes logic decisions
- (c) Works binary algebra
- 54. The logic behind 'NOR' gate is that it gives
  - (a) High output when both the inputs are low
  - (c) High output when both the inputs are high

The following configuration of gate is equivalent to

- 55. Boolean algebra is essentially based on
  - (a) Truth

56.

(b) Logic

- (b) Allows electrons flow only in one direction
- (d) Alternates between 0 and 1 values

[CPMT 1999, AFMC 1999]

- (b) Low output when both the inputs are low
- (d) None of these

[AIIMS 1999]

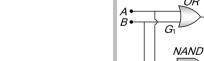
[BHU 2000]

(c) Symbol

(d) Numbers

AND

[AMU 1999]



[CBSE PMT 1998]

- (a) NAND
- (b) XOR
- (c) OR
- (d) None of these
- 57. The truth-table given below is for which gate

A 0 0 1

B 0 1 0

C 1 1 1 0

(a) XOR

(b) OR

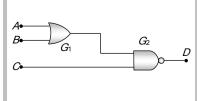
(c) AND

(d) NAND

58. For the given combination of gates, if the logic states of inputs A, B, C are as follows A = B = C = 0 and A = B = 1, C = 0 then the logic states of output D are [AMU 1998]

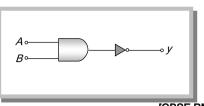
(a) 0, 0

(b) 0, 1

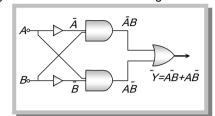


## 190 Valve & Digital Electronics (c) 1, 0 (d) 1, 1 59. The truth table shown in figure is for [Pb. CET 1998] A 0 B 0 Y 1 0 (a) XOR (b) AND (c) XNOR (d) OR 60. Which one of the following gates can be served as a building block for any digital circuit [CPMT 1996] (a) OR (b) AND (c) NOT (d) NAND 61. A truth table is given below. Which of the following has this type of truth table [CBSE PMT 1996] B 0 y 1 0 (a) XOR gate (d) OR gate (b) NOR gate (c) AND gate 62. The combination of 'NAND' gates shown here under (figure) are equivalent to [Haryana CEET 1996] (b) An AND gate and a NOT gate respectively (a) An OR gate and an AND gate respectively (c) An AND gate and an OR gate respectively (d) An OR gate and a NOT gate respectively. 63. The following truth table corresponds to the logic gate [BHU 1994] (d) XOR (a) NAND (b) OR (c) AND [NSEP 1994] 64. Given below are four logic gate symbol (figure). Those for OR, NOR and NAND are respectively (a) 1, 4, 3 (b) 4, 1, 2 (c) 1, 3, 4 (d) 4, 2, 1 65. Given below are symbols for some logic gates (i) (iv) (ii) (iii) The XOR gate and NOR gate respectively are [AFMC 1994] (a) 1 and 2 (b) 2 and 3 (c) 3 and 4 (d) 1 and 4

- 66. What is the name of the gate obtained by the combination shown in figure
  - (a) NAND
  - (b) NOR
  - (c) NOT
  - (d) XOR
- 67. Which of the following represent correctly the truth table in of the configuration



[CBSE PMT 1979]



- (a) 0 0

В

0 (c)

В

0

- 68. The combination of the gates shown in the fig. produces
  - (a) OR gate
  - (b) AND gate
  - (c) NOR gate
  - (d) XOR gate
- The expression y in the following circuit is 69.

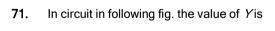


- (b) B + ACD
- (c) AB + CD
- (d) A + B + C + D

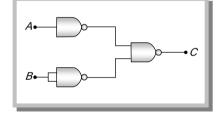


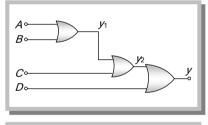


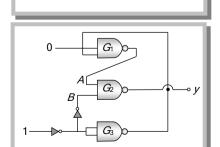
- (b)  $(A.B) + (\overline{A}.\overline{B})$
- (c)  $(A+B).(\overline{A.B})$
- (d)  $(A+B)(\overline{A}+\overline{B})$

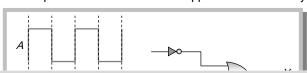


- (a) 0
- (b) 1
- (c) Fluctuates between 0 and 1
- (d) Indeterminate as the circuit can't be realised
- 72. In a given circuit as shown the two input waveform A and B are applied simultaneously. The resultant waveform Y is









## 192 Valve & Digital Electronics









- 73. What is the output of the combination of the gates shown in the fig. below
  - (a) A + A.B
  - (b)  $(A+B)\overline{A+B}$
  - (c)  $(A.B) + (\overline{A}.\overline{B})$
  - (d)  $(A+B).(\overline{A.B})$
- 74. The combination of gates shown below produces
  - (a) AND gate
  - (b) XOR gate
  - (c) NOR gate
  - (d) NAND gate
- 75. The circuit shown in figure is used to realise a logic gate. The gate is



- (b) NOT
- (c) AND
- (d) None of these
- 76. The circuit shown in fig. is used to realise a logic gate. The gate is



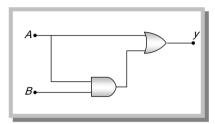
- (b) NOT
- (c) AND
- (d) None of the above
- 77. The shows two NAND gates followed by a NOR gate. The system is equivalent to the rollowing logic gate

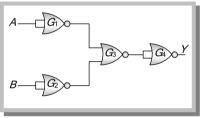


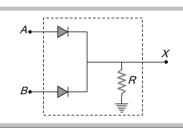
- (b) AND
- (c) NAND
- (d) None of these
- 78. The Boolean expression for the output f of the combination of logic gates shown in fig. is

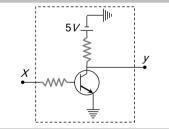


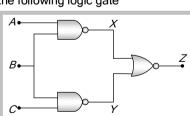
(b) 
$$A..\overline{B} + \overline{A}.B$$

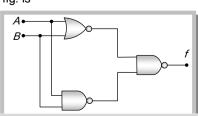










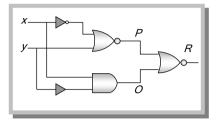




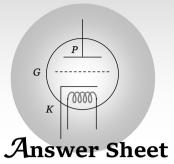




- (c)  $A + B..\overline{A} + \overline{B}$
- (d) None of these
- **79.** Figure gives a system of logic gates. From the study of truth table it can be found that to produce a high output (1) at *R*, we must have
  - (a) X = 0, Y = 1
  - (b) X=1, Y=1
  - (c) X = 1, Y = 0
  - (d) X = 0, Y = 0







	Juiswei blicet																		
Assignments																			
1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20
c	С	a	b	b	b	c	b	a	a	c	b	b	c	d	b	b	d	С	c
21	22	23	24	25	26	27	28	29	30	31	32	33	34	35	36	37	38	39	40
b	С	b	b	b	b	d	d	c	С	a	С	d	a	a	d	c	a, d	c	d
41	42	43	44	45	46	47	48	49	50	51	52	53	54	55	56	57	58	59	60
c	d	С	С	С	d	d	a	С	d	b	d	a	a	b	b	d	d	С	d
61	62	63	64	65	66	67	68	69	70	71	72	73	74	75	76	77	78	79	
b	a	b	С	b	a	b	a	d	a	a	a	a	d	a	b	b	С	С	